

Utilizing SCHOTTKY Rectifier Die In Assembly

by Bret Daniels

Introduction

This application note describes the Schottky rectifiers available from International Rectifier in die and wafer form. These epitaxial diode die feature a proprietary, high reliability planar technology utilizing a guard ring structure for maximized ruggedness. Hybrid packaging of these die results in substantial savings in weight and volume compared to standard packaging, as well as significant improvements in electrical performance, particularly lead inductance. Most of the same parts are available in finished packages; thus, development work and evaluation can be easily performed before converting the design for die application. A cross reference of packaged product to die part numbers is included in this application note.

Characteristics

Schottky die sizes presently available from International Rectifier are summarized in Table 1. These sizes range from 43.3 (1.100) to 275 (6.985) mil/side (mm/side). Sizes 43.3 and 66.1 are available only in wafer form while all others are available in both wafer and die forms. The evolution of International Rectifier Schottky diodes has resulted in four unique processes and six voltage grades. The *OR'ing*, *Low V_f Efficient*, *Standard*, and *"830"* processes have each been optimized to minimize power dissipation based upon the electrical and thermal requirements of various applications and operating modes. The *six voltage grades* available are 15V, 30V, 45V, 60V, 100V, and 150V.

Probing

Because of limitations when electrical probing in die form, some of the specifications of equivalent packaged devices cannot be tested or guaranteed in die form. Typically, these are high current forward characteristics, high temperature characteristics, surge capability (I_{FSM}), thermal resistance (R_{thJC}), series inductance (L_S), and avalanche (E_{AS} and I_{AR}). However, each wafer is 100% probed at room temperature for maximum reverse voltage (V_R), maximum reverse leakage current (I_R), and low current forward voltage drop (V_F).

During electrical probing, the rejected die are inked for identification. The wafer is then cut and the die mechanically separated. The rejected die are discarded and the remaining die are 100% visually inspected, loaded into wafer pack trays, and packed for shipment.

Handling and Shipping

Schottky die from International Rectifier are classified as non-static sensitive devices but are packaged in conductive trays for convenience. The chip tray capacities for each die size are shown in Table 1. These trays are then sealed in electrostatic shielding bags for shipment. Wafers are shipped in non-conductive, polyethylene wafer carriers.

Once opened, the die must be stored in a dry, inert atmosphere, such as nitrogen, prior to assembly. Die should be handled with DuPont Teflon-tipped vacuum

pencils to prevent mechanical damage. Any non-conformance to the electrical or visual inspection specifications in this application note must be reported in writing to International Rectifier within 30 days after shipment of the lot. International Rectifier assumes no responsibilities for die which have been subjected to further processing, such as mount-down, wire-bonding, or encapsulation. In the interest of product improvement, IR reserves the right to make design or processing changes without prior notice.

Visual Inspection of Die

International Rectifier Schottky rectifier die are designed to meet the visual inspection criteria of Mil-Standard 750, Method 2072, and are visually screened to a 0.04% AQL level.

Mounting Backside (Cathode) of Die

The Schottky die have a titanium/nickel/silver cathode metallization which is suitable for either solder paste or solder preform mounting using solders such as 92.5%/5%/2.5% Pb/In/Ag solder. It is recommended that solders containing silver are used due to silver dissolution of the backside metal in the absence of silver in the solder.

Any of the commonly used header or substrate materials, such as copper and copper-plated beryllia or alumina, are acceptable. The substrate must be free of oxides prior to assembly either by chemical cleaning or hydrogen pre-firing techniques. Mounting of Schottky die is generally accomplished in a profiled belt furnace or by using a hotplate reflow technique. Infrared or vapor phase reflow are also acceptable methods for die mounting. If using solder preforms or solder paste, cleaning must always be performed afterwards.

The furnace zone setting will depend upon hybrid mass, material, fixturing, and belt speed. The Schottky die temperature must not exceed 400°C, nor be in the range of 350 to 400°C for greater than one minute. A clean furnace of hydrogen atmosphere is recommended, although an atmosphere of nitrogen or forming gas (nitrogen-hydrogen, 85%-15%) is acceptable.

It is also possible to mount the die using conductive adhesives, although this is not currently used in production at International Rectifier.

Molybdenum Tabs

In solder applications, due to thermal expansion stresses exerted on the larger die sizes (200 mil/side and greater), International Rectifier recommends the use of molybdenum or other thermally matched tabs on the anode and cathode. The selection of tab material and/or plating must be such that it can be soldered to the silver metallization of the top and bottom metals.

International Rectifier offers standard options of molybdenum tabs soldered to the anode, cathode, or both. These are available in both round and square configurations and various sizes appropriate for a particular die size. These options are listed in Table 2. To order die with molybdenum tabs add the suffix number of the option required to the end of the die part number.

Anode Connection

Electrical connection to the anode should be a solder connection for all devices with silver top metallization. For all parts with aluminum top metallization, electrical connection to the anode is by ultrasonic bonding with aluminum wire. The wire diameter and number of wires should be chosen to suit the current requirements. For enhanced reliability, all copper piece parts that come into contact with the anode metallization must be nickel-clad or nickel-plated to eliminate copper contact with the Schottky barrier.

Caution must be exercised during wire bonding to ensure that the bonding footprint remains within the bonding pad area; otherwise, device failure can result. The bonding pad area is centered on the die and the outside edges of the die are not part of the bonding area so neither solder, in the case of silver metallization, nor wire, in the case of aluminum metallization, may make contact with the perimeter. The bonding pad area is different for each die size and the dimensions of each are listed in Table 1.

Likewise, wire bonding equipment settings should be optimized and a wire pull test performed (e.g., see Method 2037, Mil Standard 750) to monitor wire bond strength uniformity. Destructive sample testing and 100% non-destructive testing is recommended. Re-bonding of wire bond rejects can be performed although decreased yield can be expected from such reworks.

Encapsulation

Prior to encapsulation, the die or assembly should be kept in a moisture-free environment. For non-hermetic packaging, a semiconductor grade silicone elastomer may be applied. Cleaning of the die or assembly prior to coating is recommended. Immediately prior to encapsulation, especially for hermetic packages, a 150°C, two-hour bake should be performed to remove any surface moisture. Capping of hermetic packages should be performed in a dry-nitrogen atmosphere.

Conclusion

The use of Schottky rectifier die for hybrid assemblies can result in significant reduction in overall package size and significant improvements in performance and efficiency. In addition, several Schottky die can readily be mounted on the same heatsink to form circuit configurations or to parallel devices. The operational advantages of International Rectifier Schottky rectifiers, thereby, can be realized in very compact, custom package configurations. □

Note: Teflon is a trademark of DuPont.

Schottky Rectifier Die

Table I

| Wafer(1) Part Number | Die(2) Part Number | Die "A" Length/Side (in.) mm | Bond Pad "B" Length/Side (in.) mm | Anode Metallization (topside) | Process | Tray Quantity |
|----------------------------|--------------------------|------------------------------------|---|-------------------------------------|-----------|------------------|
| SC043H100SWB | N/A | (0.0433) 1.10 | (0.0362) 0.92 | Silver | 830 | N/A |
| SC043S040SWB | N/A | (0.0433) 1.10 | (0.0362) 0.92 | Silver | Standard | N/A |
| SC043S060SWB | N/A | (0.0433) 1.10 | (0.0362) 0.92 | Silver | Standard | N/A |
| SC066H100AWB | N/A | (0.0661) 1.68 | (0.0591) 1.50 | Aluminum | 830 | N/A |
| SC066H100SWB | N/A | (0.0661) 1.68 | (0.0591) 1.50 | Silver | 830 | N/A |
| SC066S040AWB | N/A | (0.0661) 1.68 | (0.0591) 1.50 | Aluminum | Standard | N/A |
| SC066S040SWB | N/A | (0.0661) 1.68 | (0.0591) 1.50 | Silver | Standard | N/A |
| SC066S060AWB | N/A | (0.0661) 1.68 | (0.0591) 1.50 | Aluminum | Standard | N/A |
| SC066S060SWB | N/A | (0.0661) 1.68 | (0.0591) 1.50 | Silver | Standard | N/A |
| SC090H045AWB | SC090H045A | 0.0900 (2.29) | 0.0700 (1.78) | Aluminum | 830 | 196 |
| SC090H150AWB | SC090H150A | 0.0900 (2.29) | 0.0700 (1.78) | Aluminum | 830 | 196 |
| SC090S045AWB | SC090S045A | 0.0900 (2.29) | 0.0700 (1.78) | Aluminum | Standard | 196 |
| SC125R015SWB | SC125R015S | | | Silver | OR'ing | 100 |
| SC125H045AWB | SC125H045A | 0.125 (3.18) | 0.105 (2.67) | Aluminum | 830 | 100 |
| SC125H045SWB | SC125H045S | 0.125 (3.18) | 0.105 (2.67) | Silver | 830 | 100 |
| SC125H100AWB | SC125H100A | 0.125 (3.18) | 0.105 (2.67) | Aluminum | 830 | 100 |
| SC125H100SWB | SC125H100S | 0.125 (3.18) | 0.105 (2.67) | Silver | 830 | 100 |
| SC125H150AWB | SC125H150A | 0.125 (3.18) | 0.105 (2.67) | Aluminum | 830 | 100 |
| SC125S030AWB | SC125S030A | 0.125 (3.18) | 0.105 (2.67) | Aluminum | Standard | 100 |
| SC125S045AWB | SC125S045A | 0.125 (3.18) | 0.105 (2.67) | Aluminum | Standard | 100 |
| SC125S045SWB | SC125S045S | 0.125 (3.18) | 0.105 (2.67) | Silver | Standard | 100 |
| SC125S060AWB | SC125S060A | 0.125 (3.18) | 0.105 (2.67) | Aluminum | Standard | 100 |
| SC150H045AWB | SC150H045A | 0.150 (3.81) | 0.130 (3.30) | Aluminum | 830 | 49 |
| SC150R015AWB | SC150R015A | 0.150 (3.81) | 0.130 (3.30) | Aluminum | OR'ing | 49 |
| SC150S045AWB | SC150S045A | 0.150 (3.81) | 0.130 (3.30) | Aluminum | Standard | 49 |
| SC175H045SWB | SC175H045S | 0.175 (4.45) | 0.155 (3.94) | Silver | 830 | 49 |
| SC175H100AWB | SC175H100A | 0.175 (4.45) | 0.155 (3.94) | Aluminum | 830 | 49 |
| SC175H100SWB | SC175H100S | 0.175 (4.45) | 0.155 (3.94) | Silver | 830 | 49 |
| SC175S045AWB | SC175S045A | 0.175 (4.45) | 0.155 (3.94) | Aluminum | Standard | 49 |
| SC175S045SWB | SC175S045S | 0.175 (4.45) | 0.155 (3.94) | Silver | Standard | 49 |
| SC175S060AWB | SC175S060A | 0.175 (4.45) | 0.155 (3.94) | Aluminum | Standard | 49 |
| SC200E045SWB | SC200E045S | 0.200 (5.08) | 0.180 (4.57) | Silver | Efficient | 36 |
| SC200H045SWB | SC200H045S | 0.200 (5.08) | 0.180 (4.57) | Silver | 830 | 36 |
| SC200H100AWB | SC200H100A | 0.200 (5.08) | 0.180 (4.57) | Aluminum | 830 | 36 |
| SC200H100SWB | SC200H100S | 0.200 (5.08) | 0.180 (4.57) | Silver | 830 | 36 |
| SC200R015SWB | SC200R015S | 0.200 (5.08) | 0.180 (4.57) | Silver | OR'ing | 36 |
| SC200S030SWB | SC200S030S | 0.200 (5.08) | 0.180 (4.57) | Silver | Standard | 36 |
| SC200S045SWB | SC200S045S | 0.200 (5.08) | 0.180 (4.57) | Silver | Standard | 36 |
| SC275H045SWB | SC275H045S | 0.275 (6.99) | 0.255 (6.48) | Silver | 830 | 25 |
| SC275H100SWB | SC275H100S | 0.275 (6.99) | 0.255 (6.48) | Silver | 830 | 25 |
| SC275S030SWB | SC275S030S | 0.275 (6.99) | 0.255 (6.48) | Silver | Standard | 25 |
| SC275S045SWB | SC275S045S | 0.275 (6.99) | 0.255 (6.48) | Silver | Standard | 25 |

(1) Die in probed un-cut, wafer form

(2) Die in probed wafer pack form

(3) All die and bond pads are square (see diagram next page)

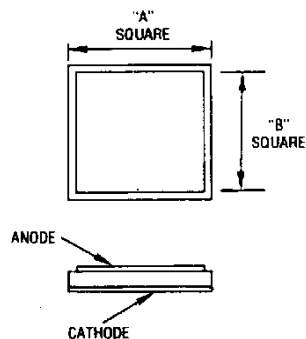
Table II

Schottky Molybdenum Tab Suffixes and Descriptions

| Suffix Number | Applicable Die Size | Top Moly (Anode) | Shape | Bottom Moly (Cathode) | Shape |
|---------------|--|-------------------|--------|-----------------------|--------|
| J01 | 0.200 (5.08) | 0.150 (3.81) dia. | Round | N/A | — |
| J02 | 0.200 (5.08) | 0.150 (3.81) dia. | Round | 0.283 (7.19) dia. | Round |
| J03 | 0.200 (5.08) | 0.150 (3.81) dia. | Round | 0.215 (5.46) dia. | Square |
| J04 | 0.200 (5.08) | N/A | — | 0.283 (7.19) dia. | Round |
| J05 | 0.200 (5.08) | N/A | — | 0.215 (5.46) dia. | Square |
| J06 | 0.200 (5.08) | 0.150 (3.81) dia. | Square | N/A | — |
| J07 | 0.200 (5.08) | 0.150 (3.81) dia. | Square | 0.283 (7.19) dia. | Round |
| J08 | 0.200 (5.08) | 0.150 (3.81) dia. | Square | 0.215 (5.46) dia. | Square |
| J09 | (These suffix numbers are for future use.) | | | | |
| J10 | | | | | |
| J11 | | | | | |
| J12 | 0.175 (4.45) | 0.125 (3.18) dia. | Round | N/A | — |
| J13 | 0.175 (4.45) | 0.125 (3.18) dia. | Round | 0.250 (6.35) dia. | Round |
| J14 | 0.175 (4.45) | 0.125 (3.18) dia. | Round | 0.190 (4.83) dia. | Square |
| J15 | 0.175 (4.45) | N/A | — | 0.250 (6.35) dia. | Round |
| J16 | 0.175 (4.45) | N/A | — | 0.190 (4.83) dia. | Square |
| J17 | (These suffix numbers are for future use.) | | | | |
| J18 | | | | | |
| J19 | | | | | |
| J20 | 0.275 (6.99) | 0.190 (4.83) dia. | Round | N/A | — |
| J21 | 0.275 (6.99) | 0.190 (4.83) dia. | Round | 0.295 (7.49) dia. | Square |
| J22 | 0.275 (6.99) | N/A | — | 0.295 (7.49) dia. | Square |

NOTES:

- 1) All dimensions are inches (mm)
- 2) Solder joints are 0.002 (0.508) thick typical
- 3) Die thickness is 0.0145 (0.3683) +/-0.0005 (0.0127)
- 4) Die length and width tolerance is +/-0.003 (0.0762)
- 5) Top moly is 0.010 (0.254) thick and bottom moly is 0.020 (0.508) thick
- 6) Moly thickness tolerance is +/-0.002 (0.0508)
- 7) Moly length and width tolerance is +/-0.002 (0.508)



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